

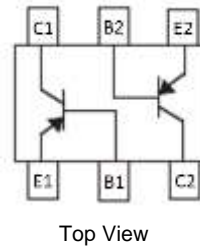
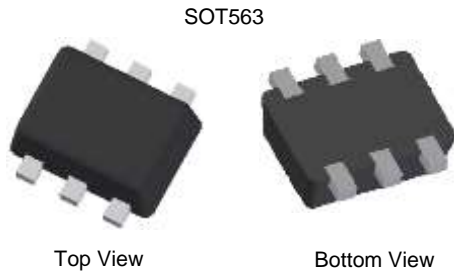
**40V DUAL PNP SMALL SIGNAL TRANSISTOR IN SOT563**

**Features**

- $BV_{CEO} > -40V$
- $I_C = -200mA$  High Collector Current
- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Ultra-Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

**Mechanical Data**

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Finish. Solderable per MIL-STD-202, Method 208
- Weight: 0.003 grams (Approximate)

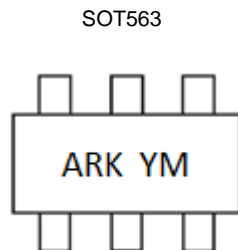


**Ordering Information** (Note 4)

Product	Status	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
MMDT3906VC-7	Active	AEC-Q101	ARK	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

**Marking Information**



ARK = Product Type Marking Code  
 YM = Date Code Marking  
 Y or  $\bar{Y}$  = Year (ex: E = 2017)  
 M or  $\bar{M}$  = Month (ex: 2 = February)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027
Code	E	F	G	H	I	J	K	L	M	N	O

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-40	V
Emitter-Base Voltage	V <sub>EBO</sub>	-6	V
Collector Current	I <sub>C</sub>	-200	mA

### Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	150	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	833	°C/W
Operating and Storage and Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

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**Thermal Characteristic and Derating Information**

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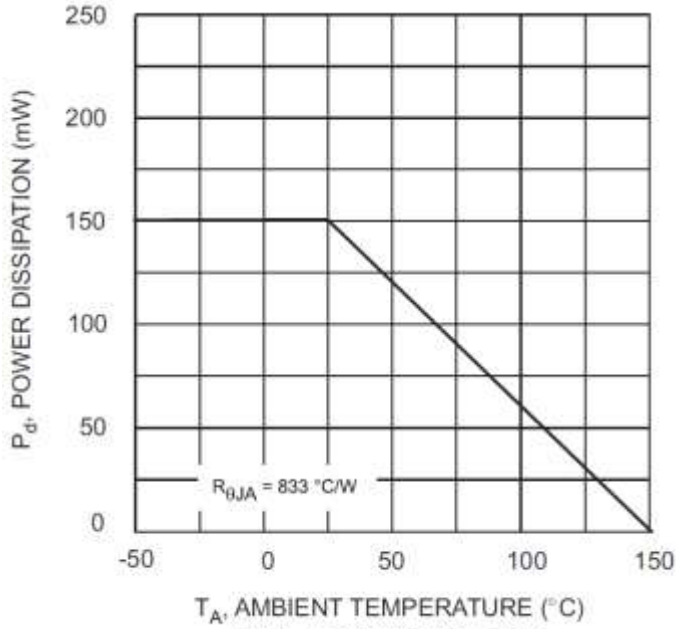


Fig. 1, Derating Curve - Total

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>					
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-40	—	V	I <sub>C</sub> = -100μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	-40	—	V	I <sub>C</sub> = -1mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-6	—	V	I <sub>E</sub> = -100μA, I <sub>C</sub> = 0
Collector Cut-Off Current	I <sub>CEX</sub>	—	-50	nA	V <sub>CE</sub> = -30V, V <sub>EB(OFF)</sub> = -3V
Base Cut-Off Current	I <sub>BL</sub>	—	-50	nA	V <sub>CE</sub> = -30V, V <sub>EB(OFF)</sub> = -3V
Emitter- Base Cut-Off Current	I <sub>EBO</sub>	—	-20	nA	V <sub>EB</sub> = -6V, I <sub>C</sub> = 0
<b>ON CHARACTERISTICS (Note 7)</b>					
DC Current Gain	h <sub>FE</sub>	60	—	—	I <sub>C</sub> = -100μA, V <sub>CE</sub> = -1V
		80	—		
		100	300		
		60	—		
		30	—		
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	—	-0.25 -0.4	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1mA I <sub>C</sub> = -50mA, I <sub>B</sub> = -5mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	-0.65 —	-0.85 -0.95	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1mA I <sub>C</sub> = -50mA, I <sub>B</sub> = -5mA
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	C <sub>OBO</sub>	—	4.5	pF	V <sub>CB</sub> = -5V, f = 1MHz, I <sub>E</sub> = 0
Input Capacitance	C <sub>IBO</sub>	—	10	pF	V <sub>EB</sub> = -0.5V, f = 1MHz, I <sub>C</sub> = 0
Input Impedance	h <sub>IE</sub>	2	12	kΩ	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1mA, f = 1kHz
Voltage Feedback Ratio	h <sub>RE</sub>	0.1	10	x 10 <sup>-4</sup>	
Small Signal Current Gain	h <sub>FE</sub>	100	400	—	
Output Admittance	h <sub>OE</sub>	3	60	μS	
Current Gain-Bandwidth Product	f <sub>T</sub>	250	—	MHz	V <sub>CE</sub> = -20V, I <sub>C</sub> = -10mA, f = 100MHz
Noise Figure	NF	—	4	dB	V <sub>CE</sub> = -5V, I <sub>C</sub> = -100μA, R <sub>S</sub> = 1kΩ, f = 1kHz
<b>SWITCHING CHARACTERISTICS</b>					
Delay Time	t <sub>D</sub>	—	35	ns	V <sub>CC</sub> = -3V, I <sub>C</sub> = -10mA, -I <sub>B1</sub> = I <sub>B2</sub> = -1.0mA
Rise Time	t <sub>R</sub>	—	35	ns	
Storage Time	t <sub>S</sub>	—	200	ns	
Fall Time	t <sub>F</sub>	—	50	ns	

Note: 7. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

**Typical Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

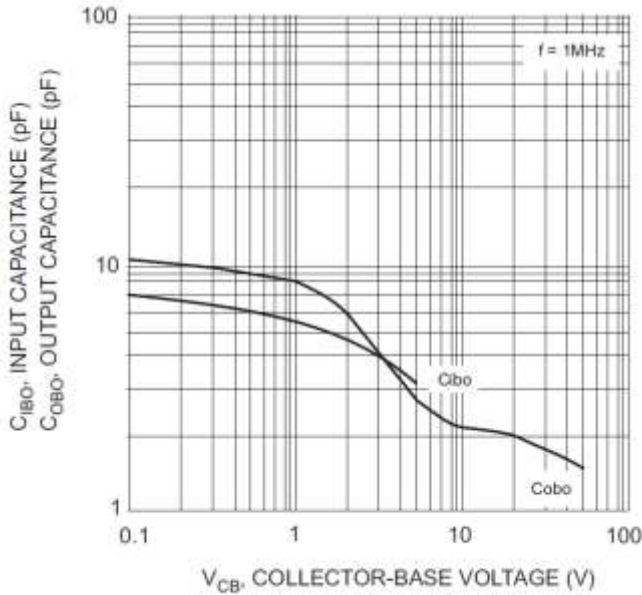


Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage

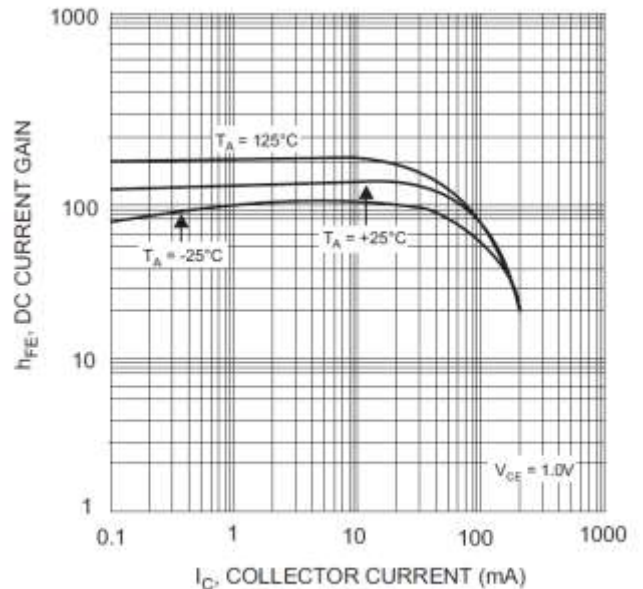


Fig. 3, Typical DC Current Gain vs. Collector Current

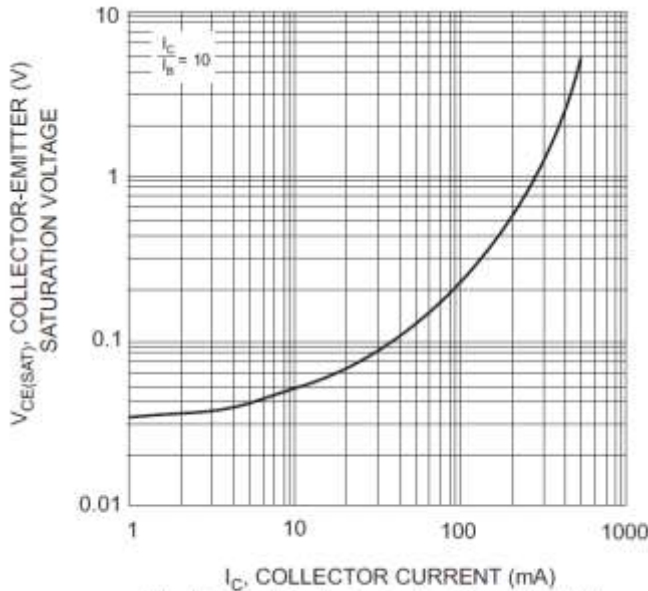


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

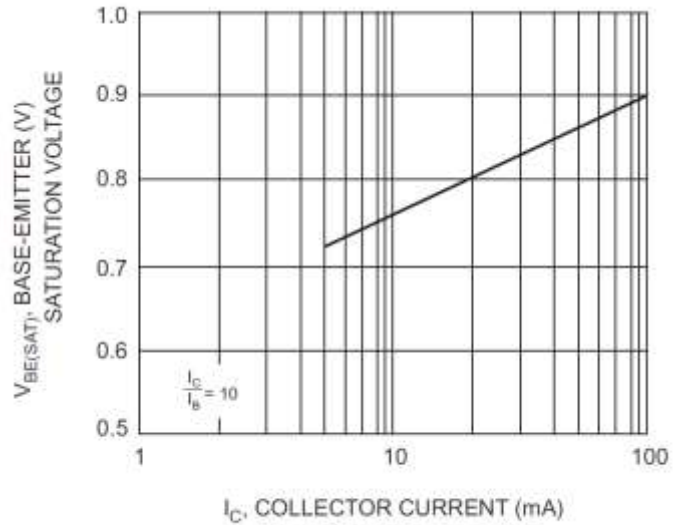
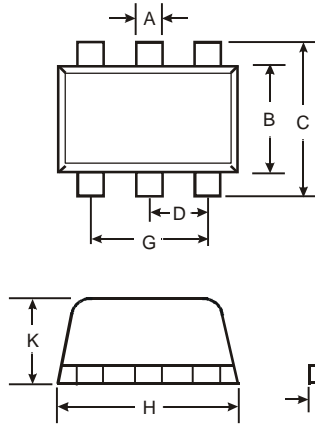


Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT563**

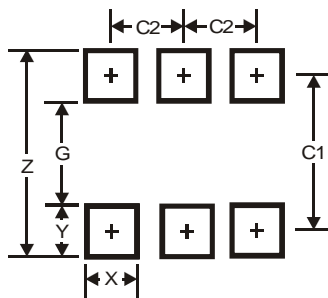


SOT563			
Dim	Min	Max	Typ
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	-	-	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT563**



Dimensions	SOT563
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5

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